

**Effect of ultrasonic treatment on the defect structure of the Si-SiO<sub>2</sub> system**

**Kropman, Daniel;** Seeman, Viktor; Dolgov, Sergei; Medvids, Arturs Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 793 - 797 <https://doi.org/10.1002/pssc.201600052> [Journal metrics at Scopus](#) [Article at Scopus](#) [Article at WOS](#)

**Interaction of point defects with impurities in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel; Mellikov, Enn;** Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

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**Understanding and control of stress at Si-SiO<sub>2</sub> interface**

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